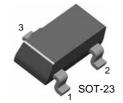


# MMBT2222AK

# **NPN Epitaxial Silicon Transistor**

## **General Purpose Transistor**





1. Base 2. Emitter 3. Collector

# Absolute Maximum Ratings $T_a = 25^{\circ}C$ unless otherwise noted

Symbol	Parameter	Value	Units
V <sub>CBO</sub>	Collector-Base Voltage	75	V
V <sub>CEO</sub>	Collector-Emitter Voltage	40	V
V <sub>EBO</sub>	Emitter-Base Voltage	6	V
I <sub>C</sub>	Collector Current	600	mA
P <sub>C</sub>	Collector Power Dissipation	350	mW
$T_{J,}T_{STG}$	Operating Junction and Storage Temperature Range	-55 ~ 150	°C

## Electrical Characteristics T<sub>a</sub>=25°C unless otherwise noted

Symbol	Parameter	Test Condition	Min.	Max.	Units
BV <sub>CBO</sub>	Collector-Base Breakdown Voltage	$I_C = 10\mu A, I_E = 0$	75		V
BV <sub>CEO</sub>	Collector-Emitter Breakdown Voltage	I <sub>C</sub> = 10mA, I <sub>B</sub> = 0	40		V
BV <sub>EBO</sub>	Emitter-Base Breakdown Voltage	$I_E = 10\mu A, I_C = 0$	6		V
I <sub>CBO</sub>	Collector Cut-off Current	$V_{CB} = 60V, I_{E} = 0$		0.01	μΑ
h <sub>FE</sub>	DC Current Gain *	$\begin{split} &V_{CE} = 10V, I_{C} = 0.1 \text{mA} \\ &V_{CE} = 10V, I_{C} = 1 \text{mA} \\ &V_{CE} = 10V, I_{C} = 10 \text{mA} \\ &V_{CE} = 10V, I_{C} = 150 \text{mA} \\ &V_{CE} = 10V, I_{C} = 500 \text{mA} \end{split}$	35 50 75 100 40	300	
V <sub>CE</sub> (sat)	Collector-Emitter Saturation Voltage *	I <sub>C</sub> = 150mA, I <sub>B</sub> = 15mA I <sub>C</sub> = 500mA, I <sub>B</sub> = 50mA		0.3 1.0	V V
V <sub>BE</sub> (sat)	Base-Emitter Saturation Voltage *	I <sub>C</sub> = 150mA, I <sub>B</sub> = 15mA I <sub>C</sub> = 500mA, I <sub>B</sub> = 50mA	0.6	1.2 2.0	V V
f <sub>T</sub>	Current Gain Bandwidth Product	I <sub>C</sub> = 20mA, V <sub>CE</sub> = 20V, f = 100MHz	300		MHz
C <sub>ob</sub>	Output Capacitance	V <sub>CB</sub> = 10V, I <sub>E</sub> = 0, f = 1MHz		8	pF
NF	Noise Figure	$I_C = 100\mu A$ , $V_{CE} = 10V$ $R_S = 1K\Omega$ , $f = 1MHz$		4	dB
t <sub>ON</sub>	Turn On Time	$V_{CC} = 30V, I_C = 150mA$ 35 $V_{BE} = 0.5V, I_{B1} = 15mA$		35	ns
t <sub>OFF</sub>	Turn Off Time	$V_{CC} = 30V, I_C = 150mA,$ $I_{B1} = I_{B2} = 15mA$		285	ns

<sup>\*</sup> Pulse Test: Pulse Width≤300μs, Duty Cycle≤2%

## **Typical Performance Characteristics**

Figure 1. DC Current Gain

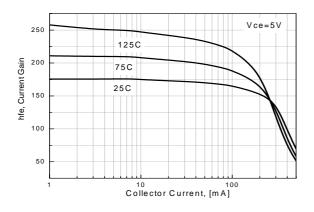


Figure 2. Collector-Emitter Saturation Voltage

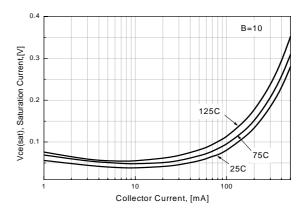


Figure 3. Base-Emitter Saturation Voltage

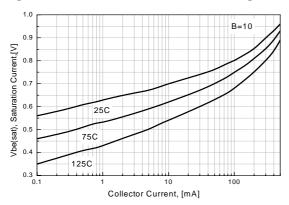


Figure 4. Collector - Base Leakage Current

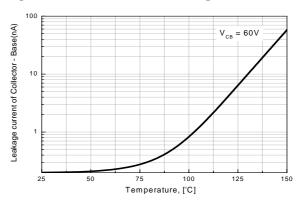


Figure 5. Output Capacitance

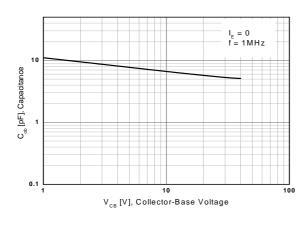
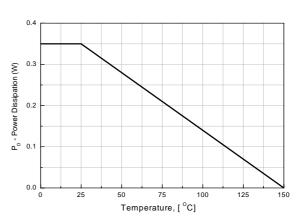


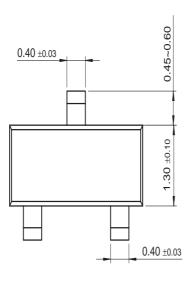
Figure 6. Power Dissipation vs
Ambient Temperature

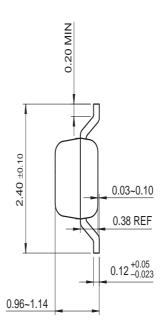


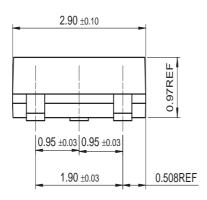
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## **Mechanical Dimensions**

# SOT-23







Dimensions in Millimeters

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DOME™	HiSeC™	MSX™	RapidConfigure™	UHC™
EcoSPARK™	I <sup>2</sup> C™	MSXPro™	RapidConnect™	UltraFET <sup>®</sup>
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